AMENDMENTS TO THE SPECIFICATION

Page 6, delete the second full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the first aspect~~any one of the first to the third aspects~~, wherein the thin film is etched while supplying at least a part of the chemical species to the thin film in a direction perpendicular to the thin film, so that the thin film is etched while an organic substance is deposited on a side wall of the resist pattern being etched by an isotropic etching component.

Page 6, delete the fourth full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the fourth~~or the fifth~~ aspect, wherein at least a part of the chemical species is supplied to the thin film in the direction perpendicular to the thin film so that an etching selectivity between the resist pattern and the thin film (thin film etch rate/resist pattern etch rate) is smaller than 1.5.

Page 6, delete the fifth full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the first aspect~~any one of the first through the sixth aspects~~, wherein a resist layer of the resist pattern has a coverage of 70% or more with respect to the thin film.

Page 6, delete the sixth paragraph bridging page 7 and insert the following paragraph:

The method of etching a chromium-based thin film according to the first aspect~~any one of the first through the sixth aspects~~, wherein the thin film is etched in presence of an organic substance other than the resist pattern if a resist layer of the resist pattern has a coverage smaller than 70% with respect to the thin film.

Page 7, delete the fourth full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the ninth ~~or the tenth~~ aspect, wherein the presence of the organic substance other than the resist pattern is established by adding an organic gas to the dry etching gas as the organic substance other than the resist pattern.

Page 8, delete the first full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the eleventh ~~or the twelfth~~ aspect, wherein the organic gas is ethanol.

Page 8, delete the second full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the ninth ~~or the tenth~~ aspect, wherein an organic polymer material is disposed in an etching chamber as the organic substance other than the resist pattern.

Page 8, delete the third full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the ninth aspect ~~any one of the ninth through the fourteenth aspects~~, wherein the thin film is etched using, as the plasma excitation power, a power lower than a plasma excitation power at which plasma density jump occurs.

Page 8, delete the fifth full paragraph and insert the following paragraph:

The method of etching a chromium-based thin film according to the first or the ninth aspect ~~any one of the first to the sixteenth aspects~~, wherein the object is a photomask blank comprising a transparent substrate and a light-shielding film made of a material containing chromium and formed on the transparent substrate.

Page 9, delete the second full paragraph and insert the following paragraph:

The method of manufacturing a photomask according to the eighteenth ~~or the nineteenth~~ aspect, wherein, by etching the light-shielding film, a pattern including a pattern of which a design size is 0.4 μm or more and 2.0 μm or less and of which a CD linearity error is 15 nm or less is formed.